

## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

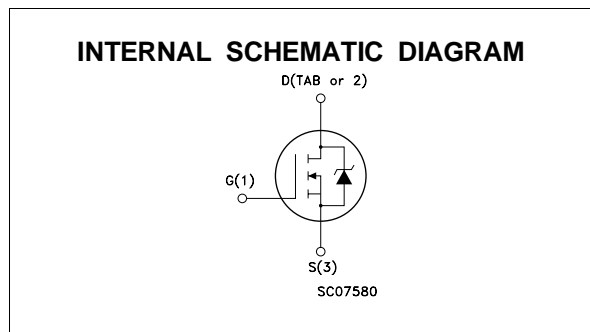
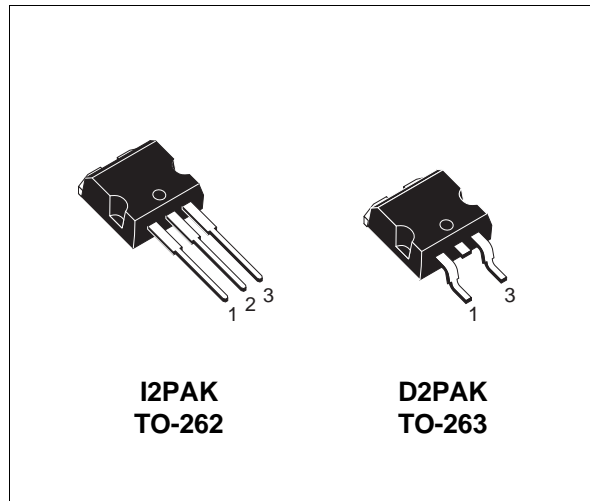
PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB15N25	250 V	< 0.25 Ω	15 A

- TYPICAL R<sub>DS(on)</sub> = 0.2 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- LOW LEAKAGE CURRENT
- APPLICATION ORIENTED CHARACTERIZATION
- THROUGH-HOLE I2PAK (TO-262) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING D2PACK (TO-263) POWER PACKAGE IN TUBE (NO SUFFIX) OR IN TAPE & REEL (SUFFIX "T4")

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY (UPS)



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	250	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	250	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	15	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	10	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	60	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	125	W
	Derating Factor	1	W/°C
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(●) Pulse width limited by safe operating area

## STB15N25

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Case-sink	Typ	0.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	15	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	40	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)	10	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%)	10	A

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	250			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C			250 1000	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 7.5 A V <sub>GS</sub> = 10 V I <sub>D</sub> = 7.5 A T <sub>c</sub> = 100 °C			0.25 0.5	Ω Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	15			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> I <sub>D</sub> = 7.5 A	5			S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1600		pF
C <sub>oss</sub>	Output Capacitance			270		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50		pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 100\text{ V}$ $R_G = 9.1\ \Omega$	$I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$		20 75	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 160\text{ V}$ $R_G = 9.1\ \Omega$	$I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$		470	A/ $\mu\text{s}$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 160\text{ V}$	$I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$		60 10 25	nC nC nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 160\text{ V}$ $R_G = 9.1\ \Omega$	$I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$		35 30 70	ns ns ns

**SOURCE DRAIN DIODE**

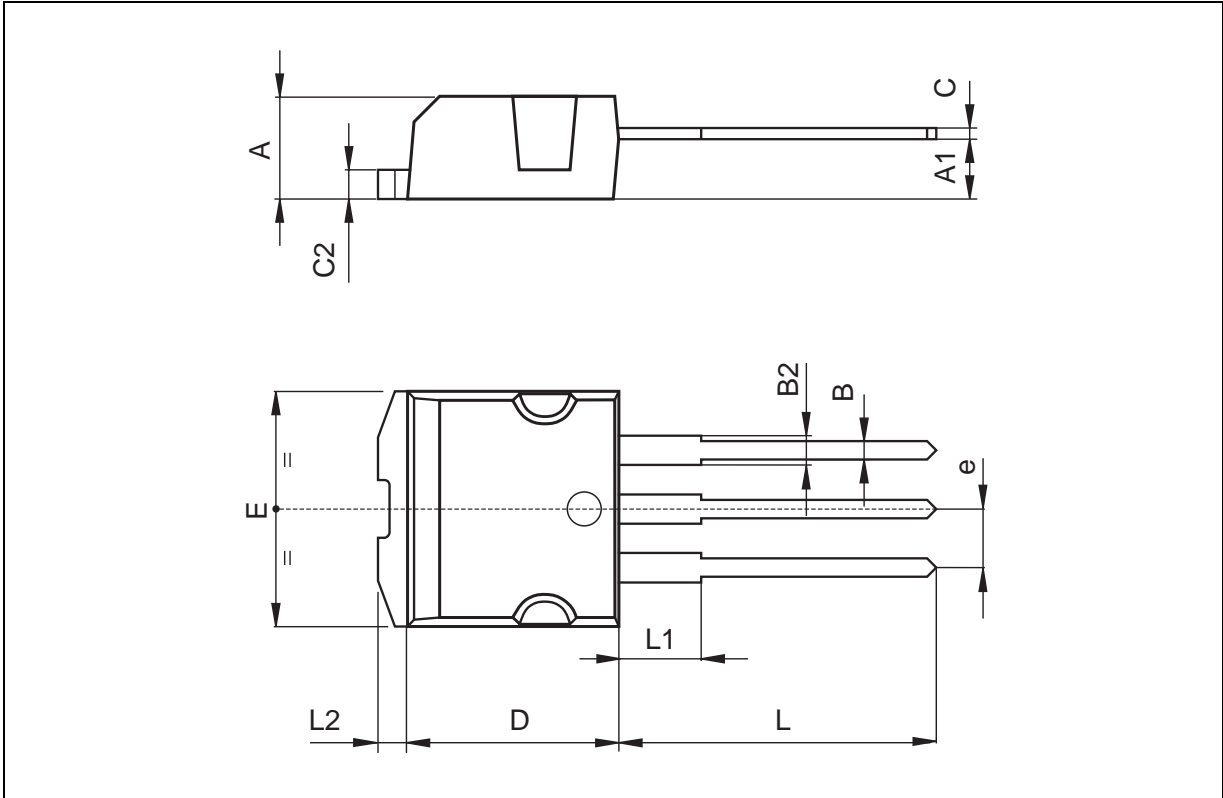
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				15 60	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 15\text{ A}$	$V_{GS} = 0$		1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 15\text{ A}$ $V_R = 100\text{ V}$	$di/dt = 100\text{ A}/\mu\text{s}$ $T_j = 150\text{ }^\circ\text{C}$		290 3 21	ns $\mu\text{C}$ A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

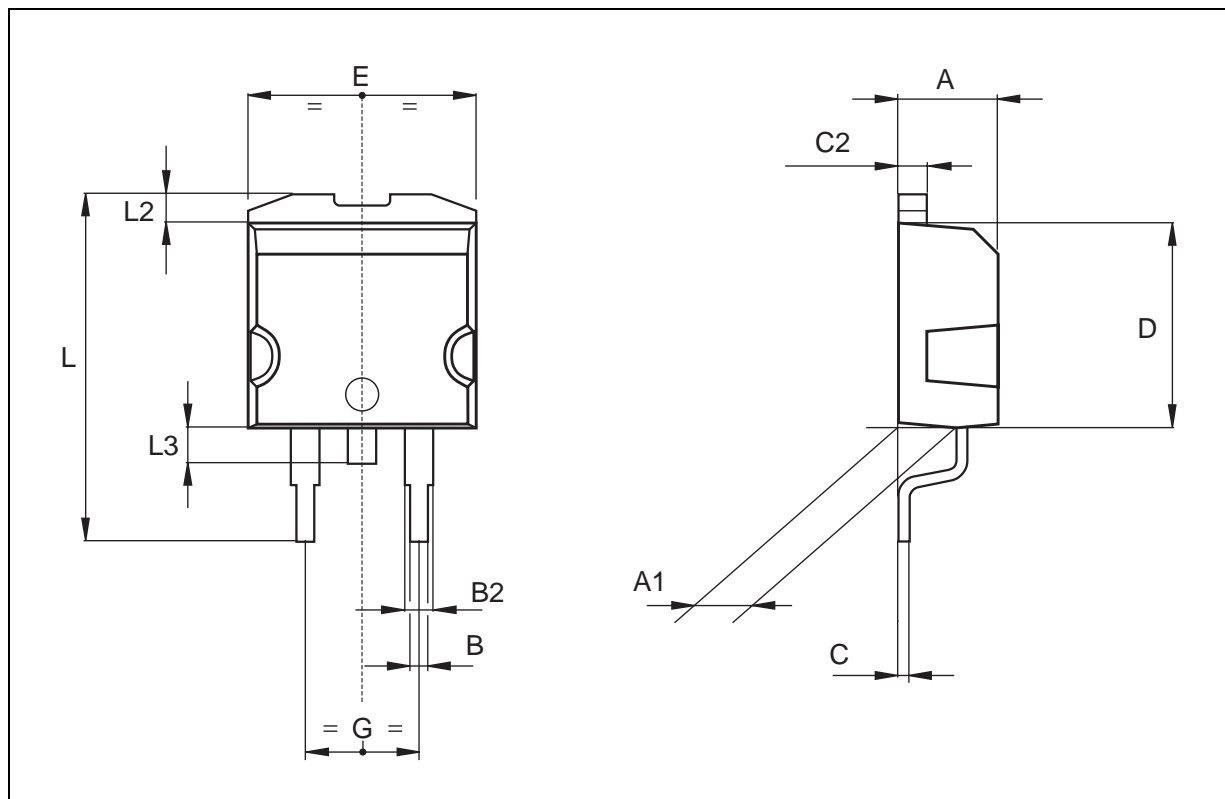
**TO-262 (I2PAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B1	1.2		1.38	0.047		0.054
B2	1.25		1.4	0.049		0.055
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	9		9.35	0.354		0.368
e	2.44		2.64	0.096		0.104
E	10		10.28	0.393		0.404
L	13.2		13.5	0.519		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.37	0.050		0.054



## TO-263 (D2PAK) MECHANICAL DATA

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A	4.3		4.6	0.169		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.25		1.4	0.049		0.055
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	9		9.35	0.354		0.368
E	10		10.28	0.393		0.404
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.37	0.050		0.054
L3	1.4		1.75	0.055		0.068



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